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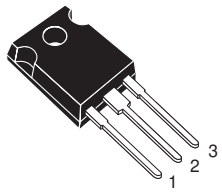
STW70N60M2

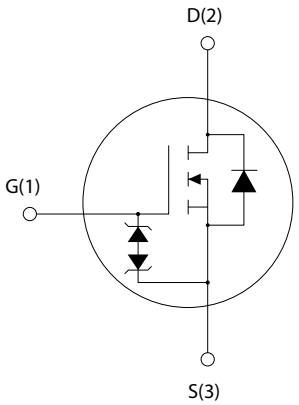
N-channel 600 V, 0.03 Ω typ., 68 A MDmesh™ M2 Power MOSFET in a TO-247 package

Datasheet – production data



TO-247

Figure 1. Internal schematic diagram



Features

Order codes	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max	I_D
STW70N60M2	650 V	0.040 Ω	68 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STW70N60M2	70N60M2	TO-247	Tube

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	68	A
I_D	Drain current (continuous) at T_C = 100 °C	43	A
I_{DM} (1)	Drain current (pulsed)	272	A
P_{TOT}	Total dissipation at T_C = 25 °C	450	W
dv/dt (2)	Peak diode recovery voltage slope	15	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 68$ A, di/dt ≤ 400 A/µs; $V_{DS\ peak} < V_{(BR)DSS}$, V_{DD}= 400 V.
3. $V_{DS} \leq$ 480 V

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.28	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	50	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	10	A
E_{AS}	Single pulse avalanche energy (starting T_j=25°C, I_D= 10 A; V_{DD}=50)	1500	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	600			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 600 V			1	µA
		V_{DS} = 600 V, T_C=125 °C			100	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 34 A		0.030	0.040	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0	-	5200	-	pF
C_{oss}	Output capacitance		-	250	-	pF
C_{rss}	Reverse transfer capacitance		-	5	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0	-	395	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0	-	3.3	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 68 A, V_{GS} = 10 V (see *Figure 15*)	-	118	-	nC
Q_{gs}	Gate-source charge		-	25	-	nC
Q_{gd}	Gate-drain charge		-	47	-	nC

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 34 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14* and *Figure 19*)	-	32	-	ns
t_r	Rise time		-	17	-	ns
$t_{d(off)}$	Turn-off-delay time		-	155	-	ns
t_f	Fall time		-	9	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		68	A
I_{SDM} (1)	Source-drain current (pulsed)		-		272	A
V_{SD} (2)	Forward on voltage	I_{SD} = 68 A, V_{GS} = 0	-	0.98	1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 68 A, di/dt = 100 A/µs V_{DD} = 60 V (see *Figure 18*)	-	520		ns
Q_{rr}	Reverse recovery charge		-	12		µC
I_{RRM}	Reverse recovery current		-	45		A
t_{rr}	Reverse recovery time	I_{SD} = 68 A, di/dt = 100 A/µs V_{DD} = 60 V, T_j = 150 °C (see *Figure 18*)	-	680		ns
Q_{rr}	Reverse recovery charge		-	18		µC
I_{RRM}	Reverse recovery current		-	50		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

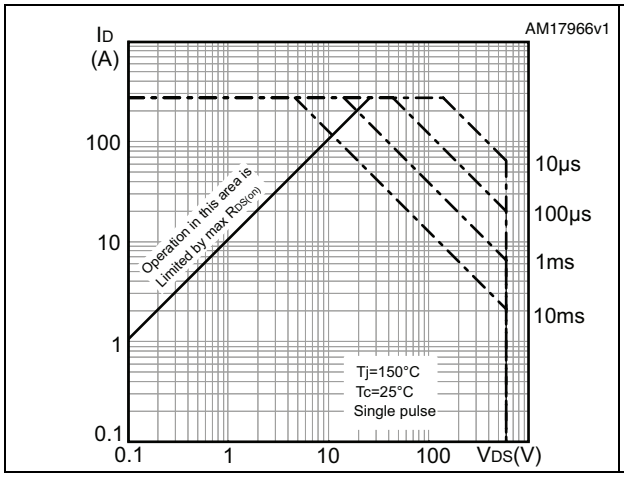


Figure 3. Thermal impedance

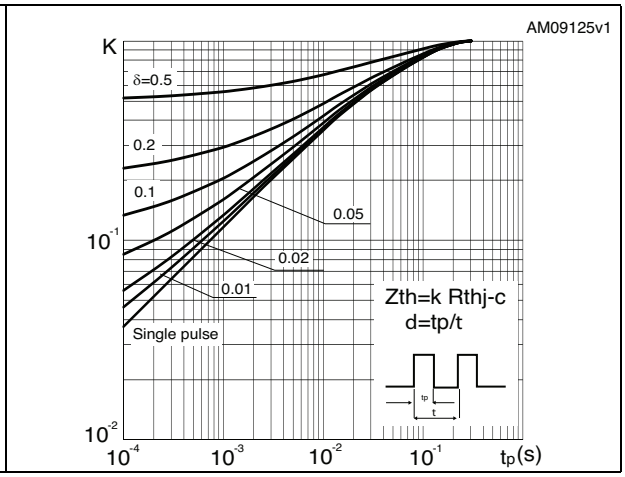


Figure 4. Output characteristics

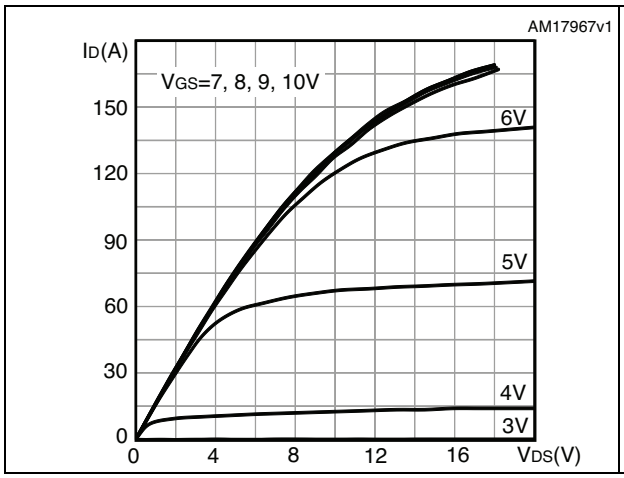


Figure 5. Transfer characteristics

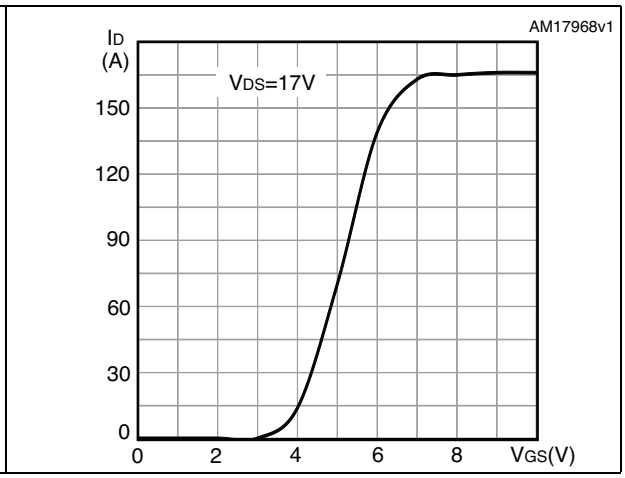


Figure 6. Gate charge vs gate-source voltage

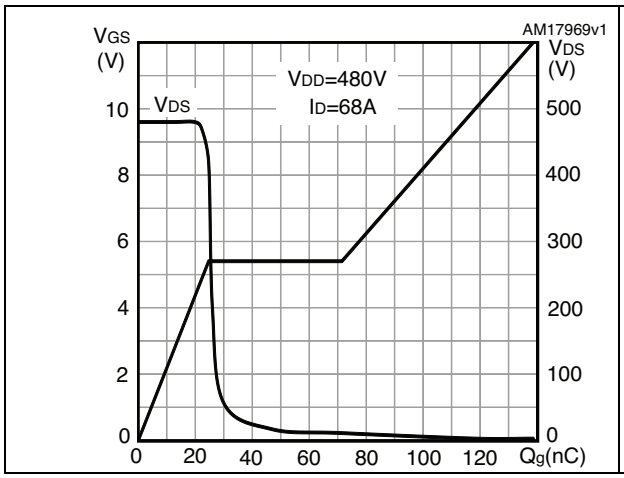


Figure 7. Static drain-source on-resistance

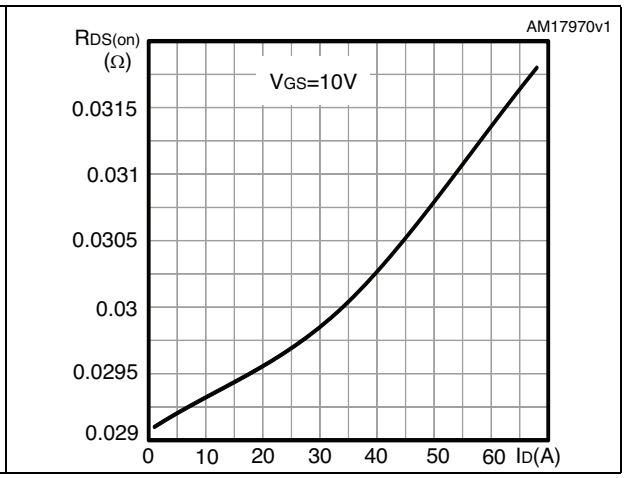


Figure 8. Capacitance variations

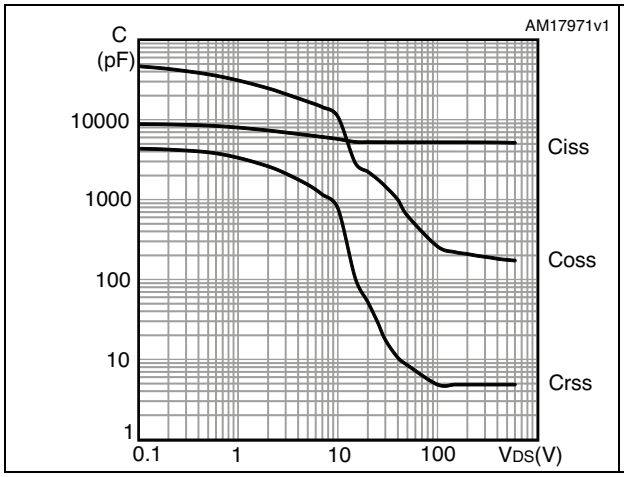


Figure 9. Output capacitance stored energy

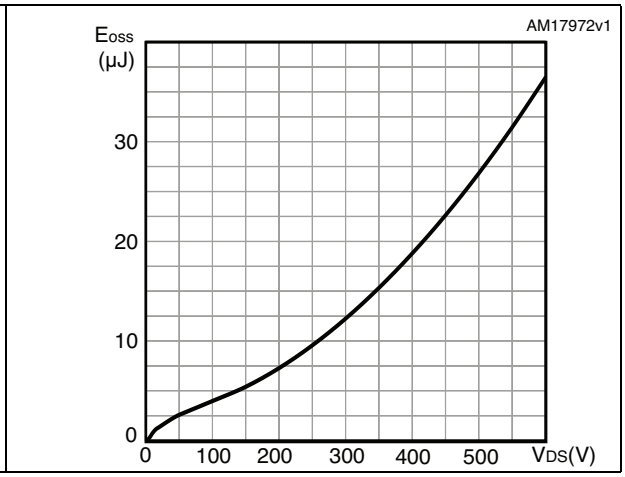


Figure 10. Normalized gate threshold voltage vs temperature

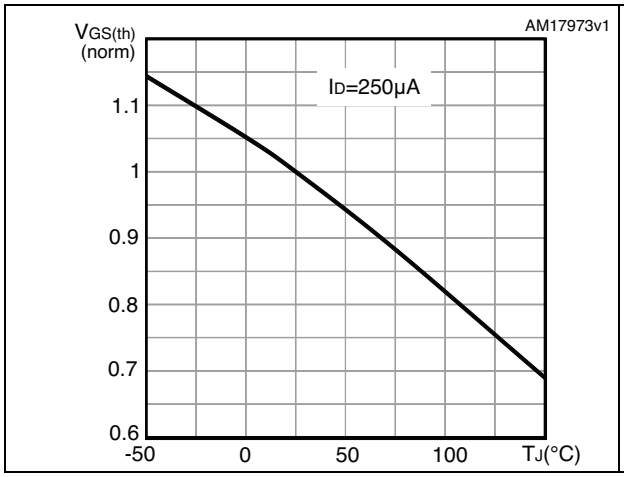


Figure 11. Normalized on-resistance vs temperature

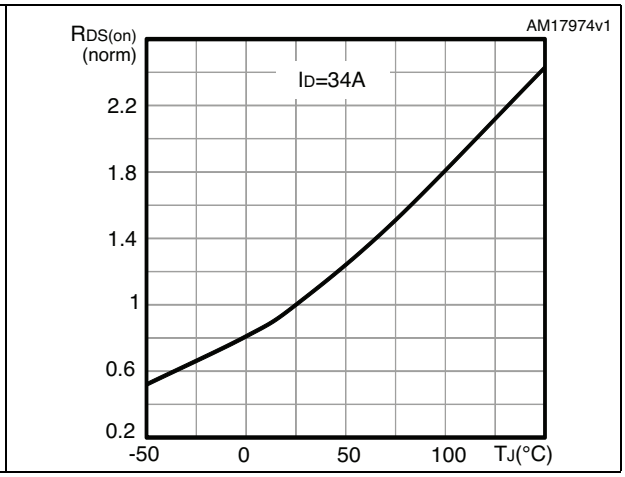


Figure 12. Normalized V_{DS} vs temperature

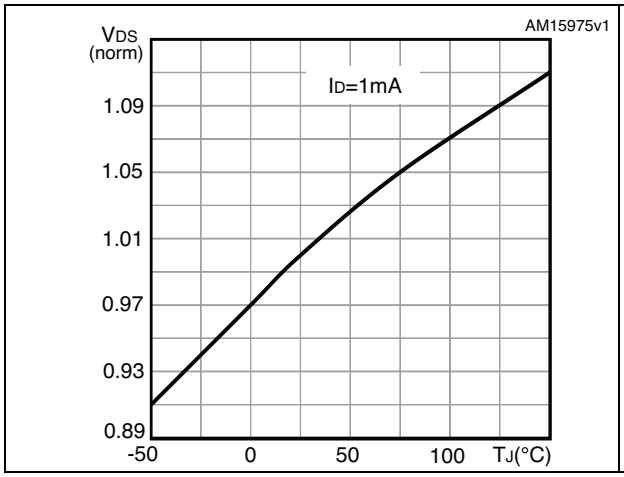
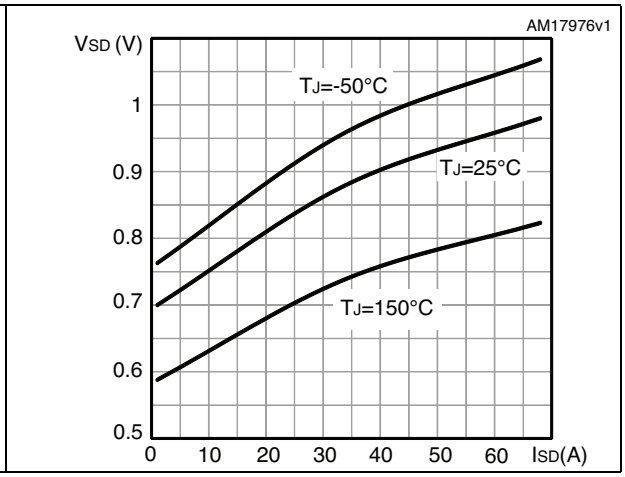


Figure 13. Source-drain diode forward characteristics



3 Test circuits

Figure 14. Switching times test circuit for resistive load

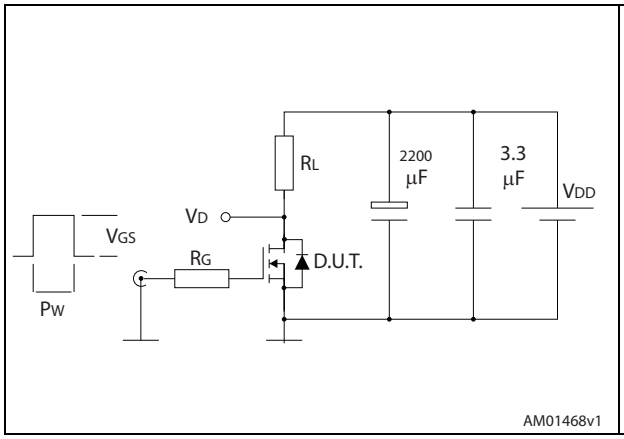


Figure 15. Gate charge test circuit

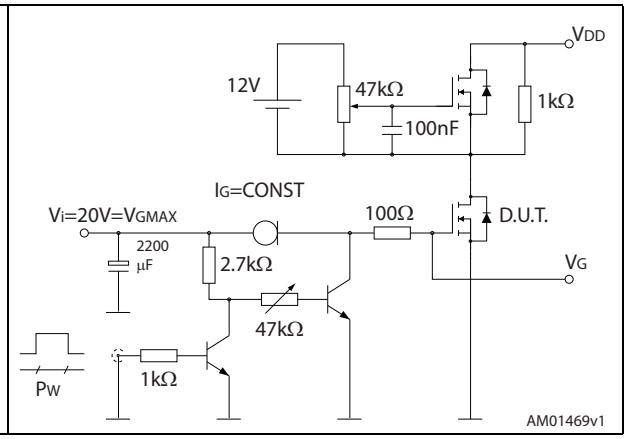


Figure 16. Test circuit for inductive load switching and diode recovery times

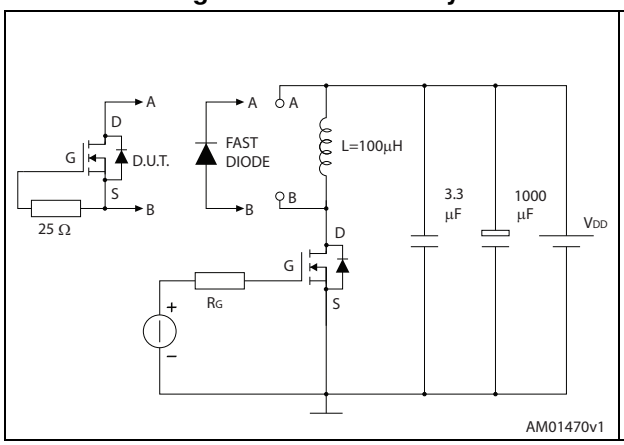


Figure 17. Unclamped inductive load test circuit

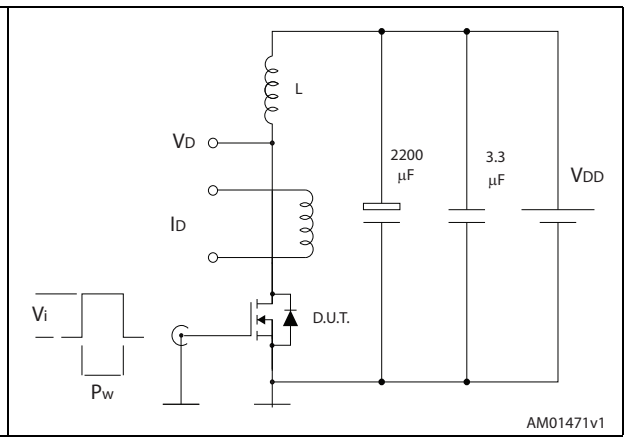


Figure 18. Unclamped inductive waveform

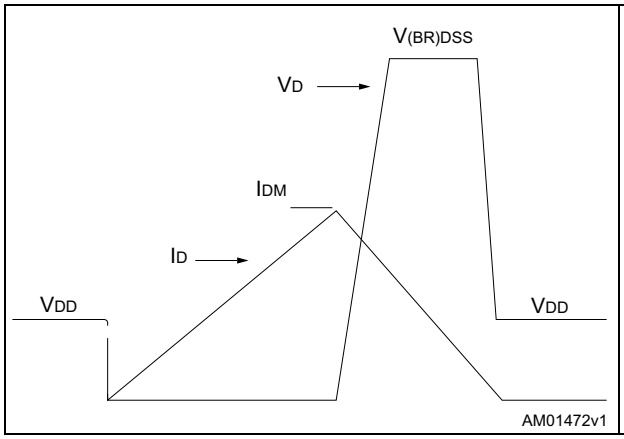
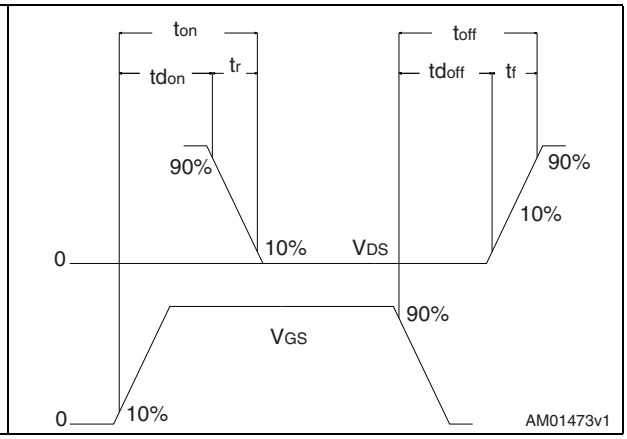


Figure 19. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*.
ECOPACK is an ST trademark.

Figure 20. TO-247 drawing

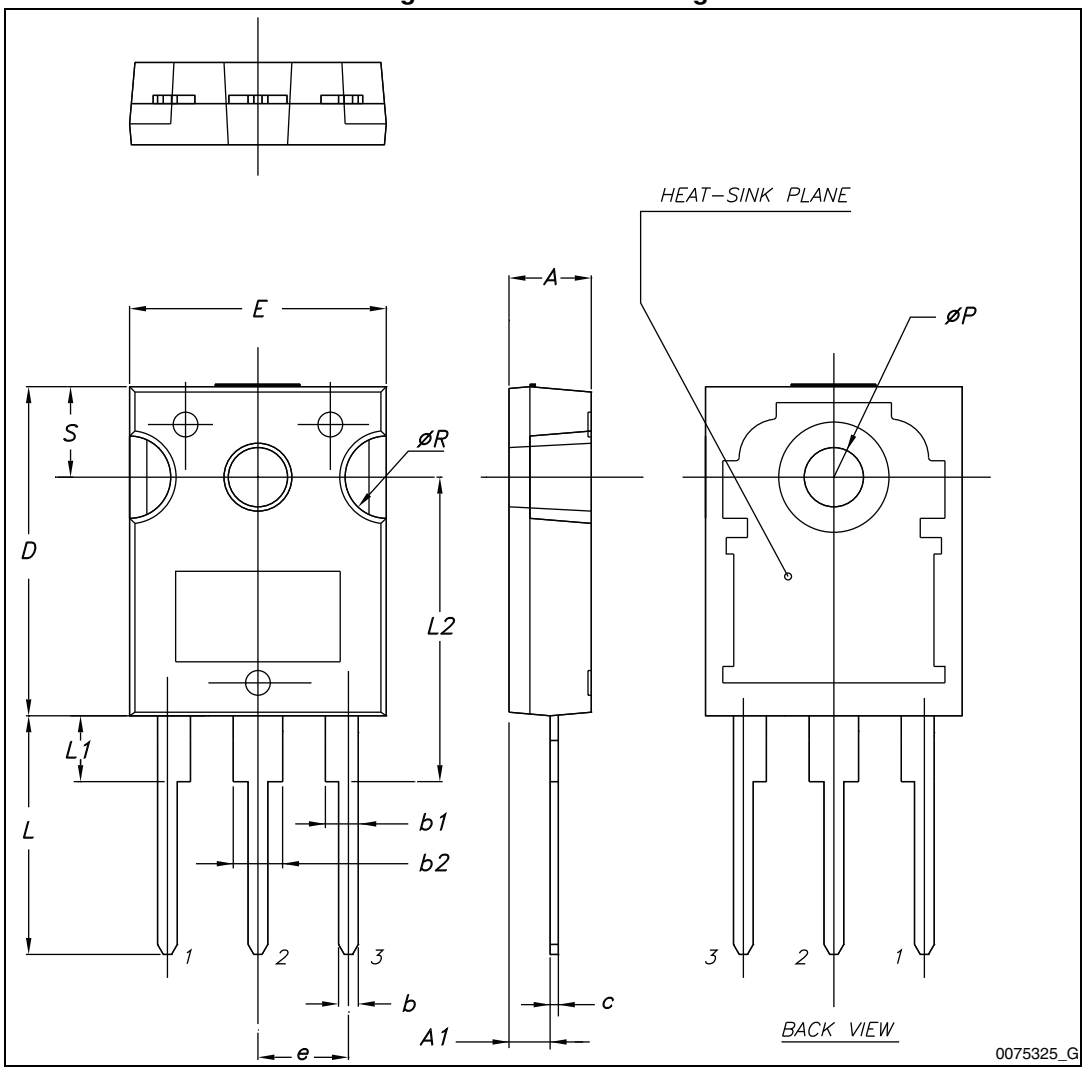


Table 9. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
∅P	3.55		3.65
∅R	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
28-Feb-2013	1	First release.
13-Mar-2013	2	– Minor text changes – Modified: test condition in *Table 7*
12-Dec-2013	3	– Modified: title – Modified: *Table 4*, $R_{DS(on)}$ typical value in *Table 5*, the entire typical values in *Table 6*, *7* and *8* – Updated: *Section 3: Test circuits* – Added: *Section 2.1: Electrical characteristics (curves)* – Minor text changes
01-Sep-2014	4	– Updated values in *Table 4* – Updated description and features in cover page – Minor text changes